

Visualizing Oxide Breakdown and Pit Initiation in Aluminum using *ex situ* Electron Microscopy

K.R. Zavadil

Sandia National Laboratories
Albuquerque, NM 87185-0888

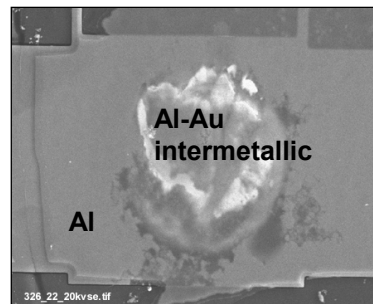
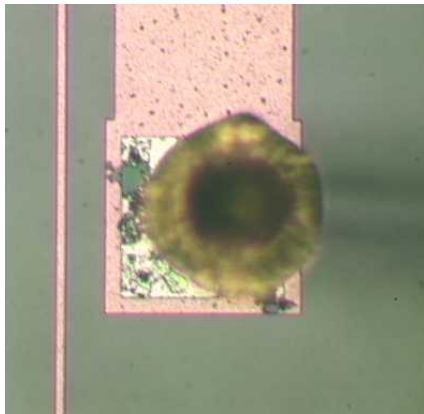
Acknowledgements: P.G. Kotula – TEM, R. Grant - SEM

DOE Basic Energy Sciences Office of Materials & Engineering Sciences

Sandia is a multiprogram laboratory operated by Sandia Corporation, a Lockheed Martin Company, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000

Why study pit initiation in aluminum?

High consequence systems: minimal separation between initiation and damage
microelectronics – nanomaterials integration & devices



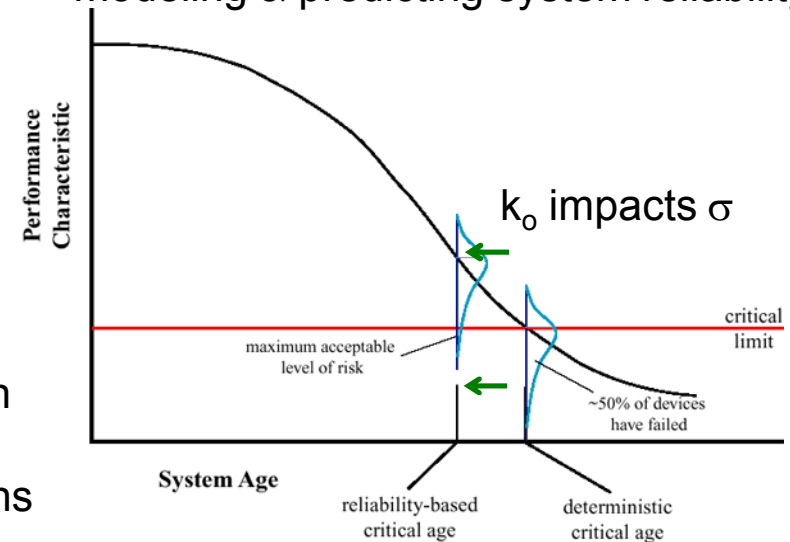
Al interconnects can undergo galvanic corrosion

rate constant (k_o) - lump sum term for unknowns

$$\frac{d(\Delta R / R_o)}{dt} = I(\text{defects})k_o P_{Cl_2}(t) \left\{ 1 - \exp \left[- \left(\frac{H(t)}{\eta} \right)^\beta \right] \right\} \exp \left[- \frac{E_a}{RT(t)} \right]$$

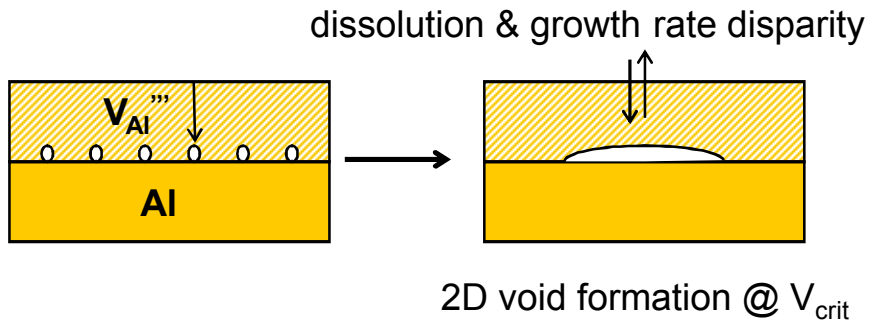
Reliability prediction requires relevant physical & chemical inputs of localized corrosion mechanisms

modeling & predicting system reliability

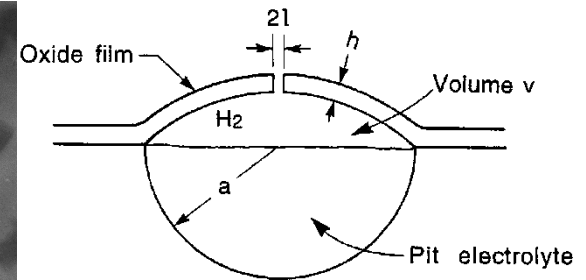
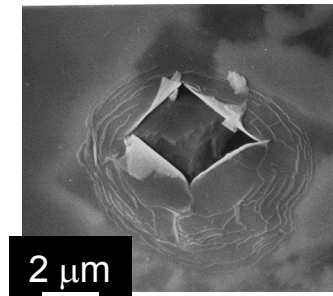


Proposed mechanisms for pit initiation

Vacancy condensation - Point Defect Model (Macdonald)

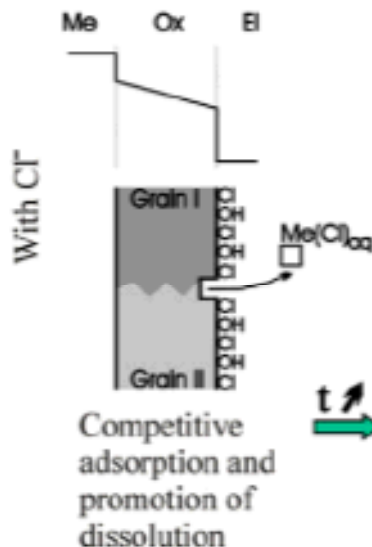


Nano-corrosion cells - Electrokinetic Model (McCafferty)

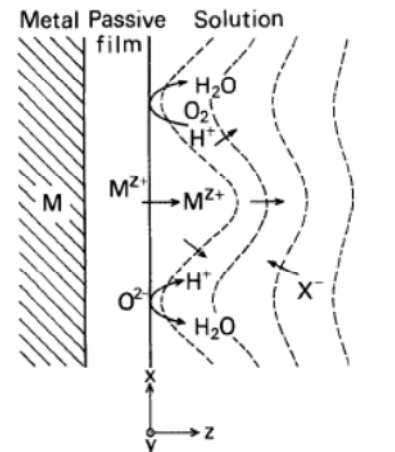


McCafferty & Natishan, 218th ECS #1322

Oxide grain boundaries - Marcus, Maurice & Strehblow



Aggressive anion and electric field perturbation - Okada

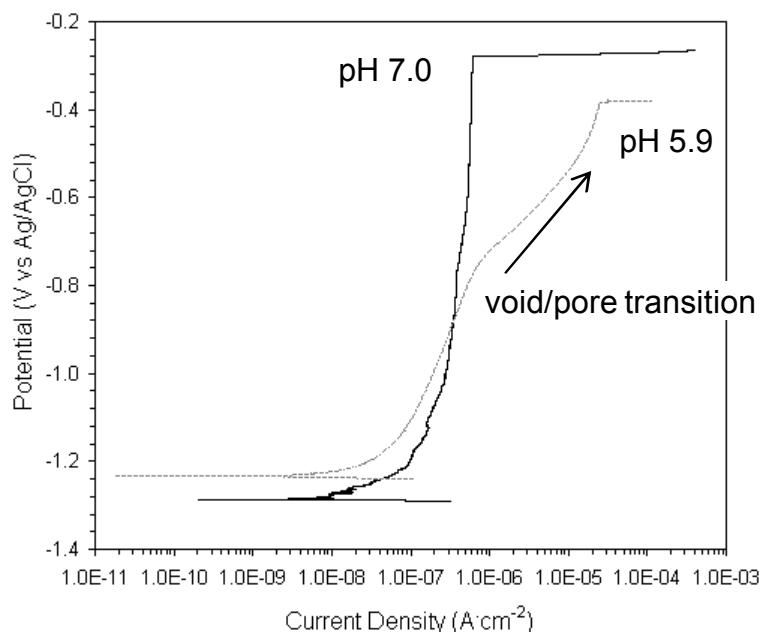


electrostriction

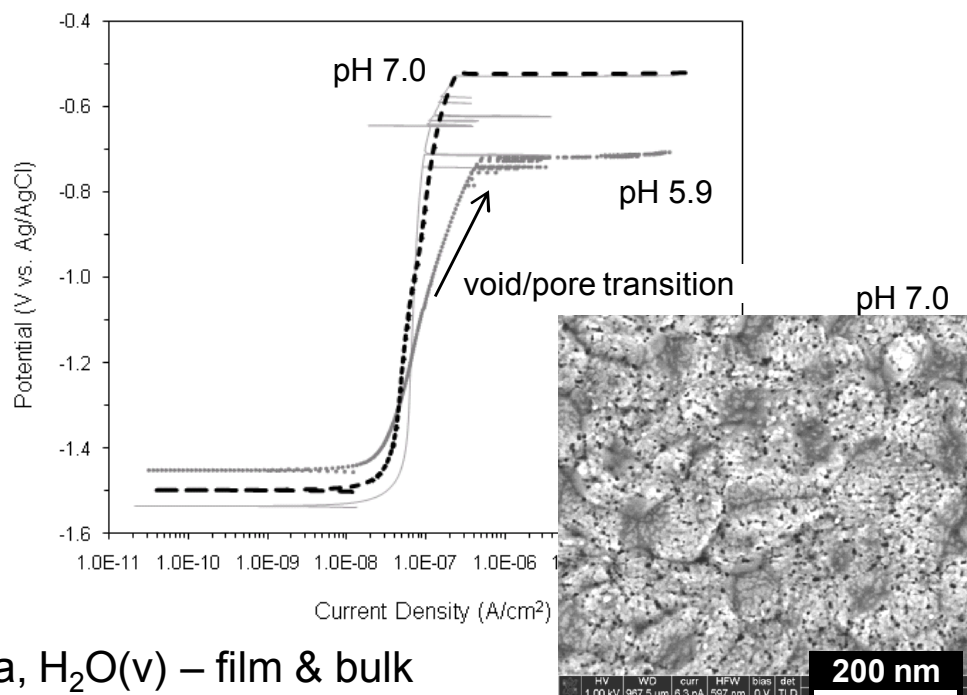
Pit initiation in an anhydrous oxide on Al coincides with oxide defect activity

~150 nm diameter grain Al(111) film in de-aerated 50 mM NaCl

Macroscale measurements at 1 cm²



Mesoscale capillary measurements at < 0.01 cm²



Initially anhydrous oxides – O₂, O plasma, H₂O(v) – film & bulk including single crystal

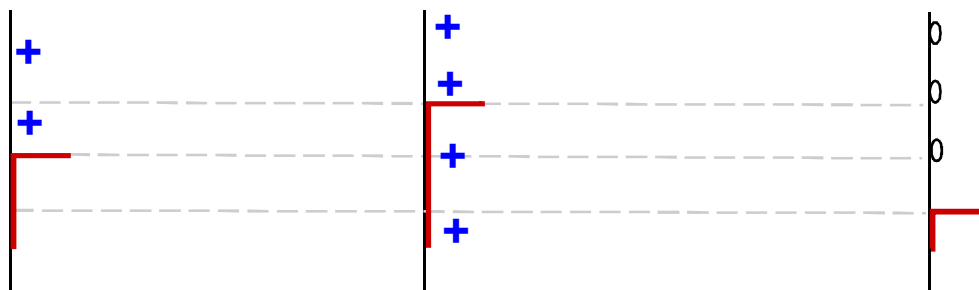
I/V response shows the presence of a proton-activated process that leads to accentuated current generation – anodic dissolution can compete with pit initiation

Void nucleation results from defect response to applied field

transport barrier

saturation

void nucleation

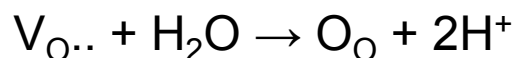


*interfacial $V_{O\cdot}$

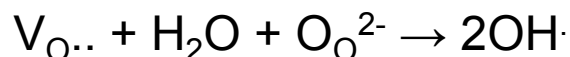
Al oxidation increases $V_{O\cdot}$

barrier relieved

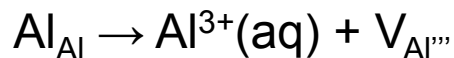
$V_{O\cdot}$ saturation through a simple equilibrium:



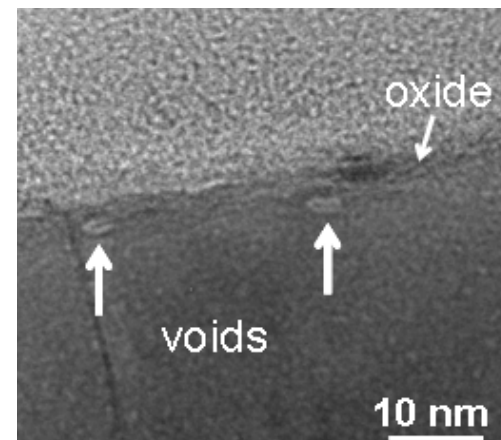
Alternate reaction to consider:



Ox:El interface barriers:



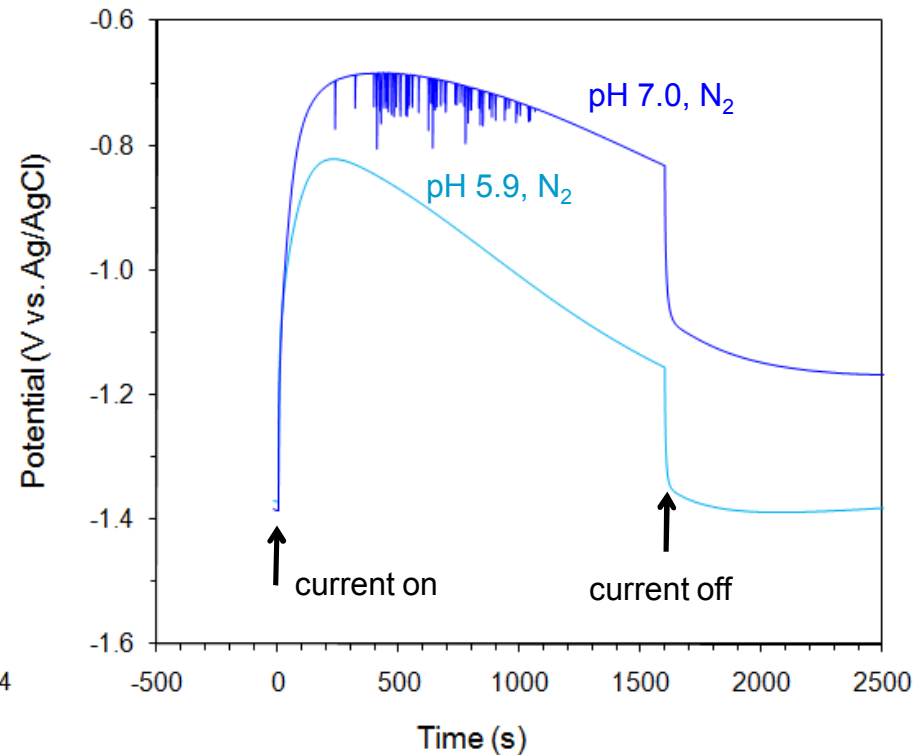
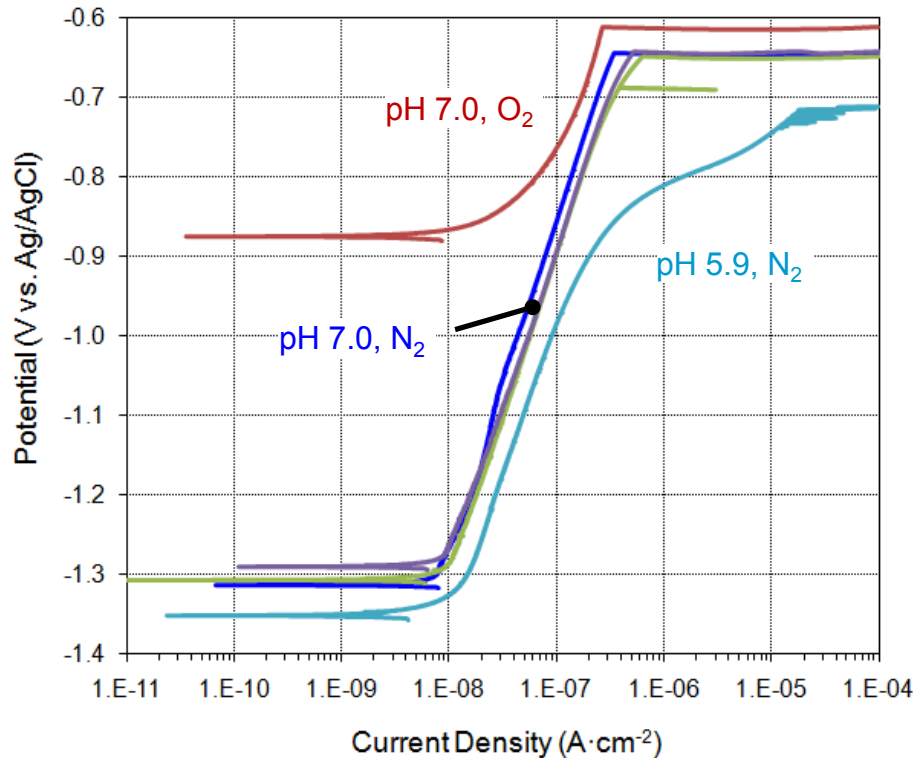
retarded by surface adsorbates or chelating species



Can voids contribute to pit initiation?

Chronopotentiometry highlights the coincidence of pitting & defect activity

700 nm thick Al(111) film in de-aerated 50 mM NaCl

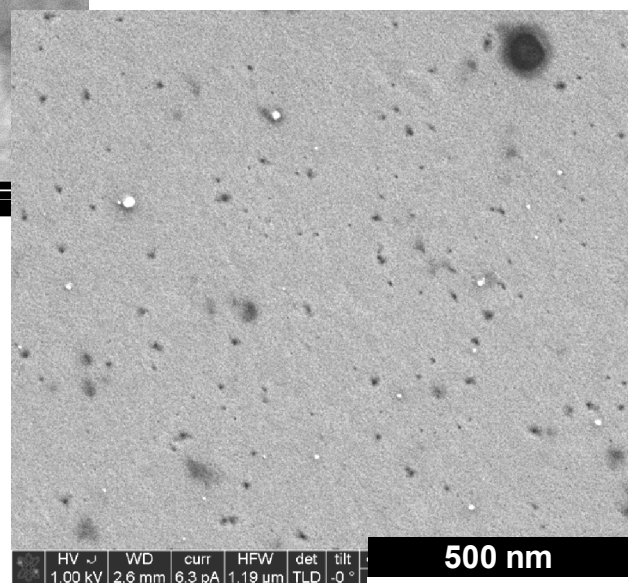
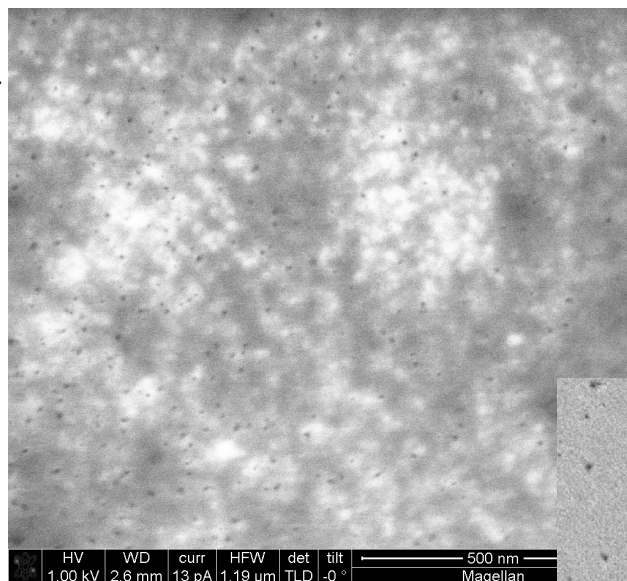
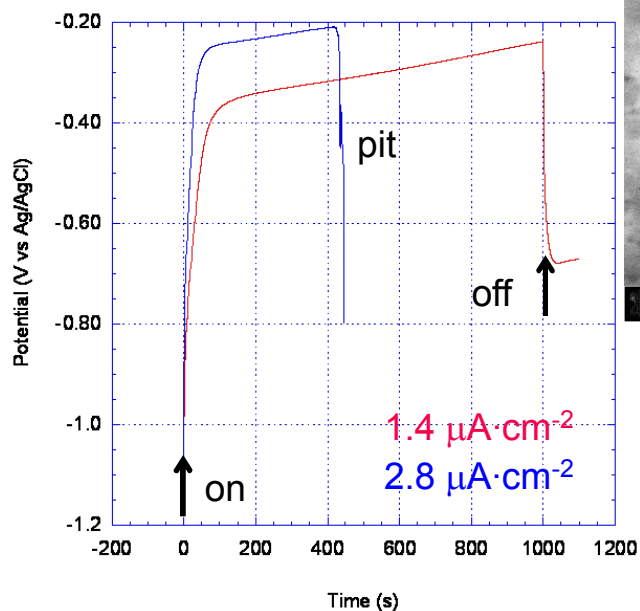


Pitting and accentuated dissolution compete

Similar defect processes operative in *not so model* oxides

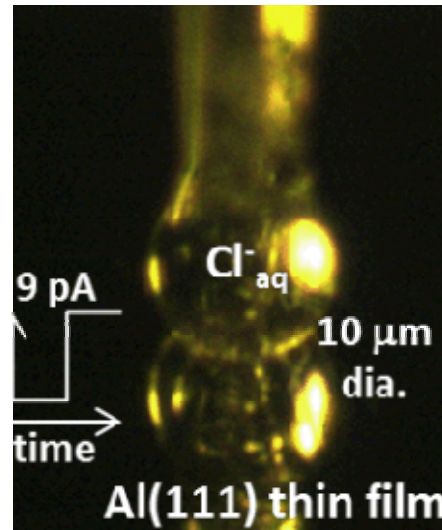
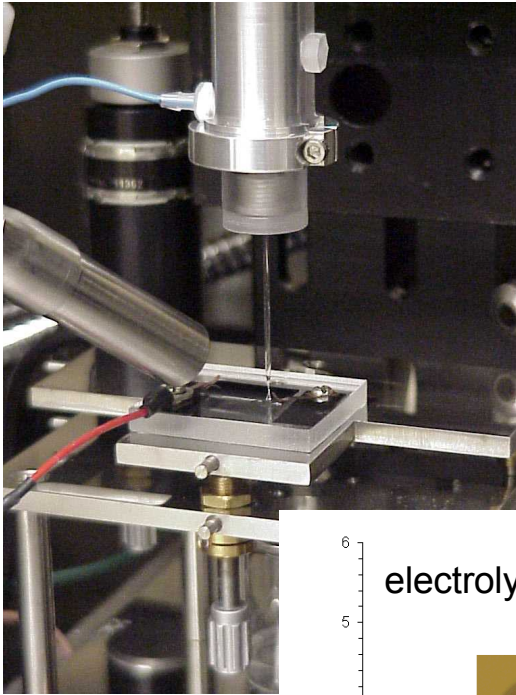
99.999% polycrystalline Al aqueous alumina (30 nm polish) – oxide allowed to dry

equilibrated 1 hour 50 mM Cl⁻

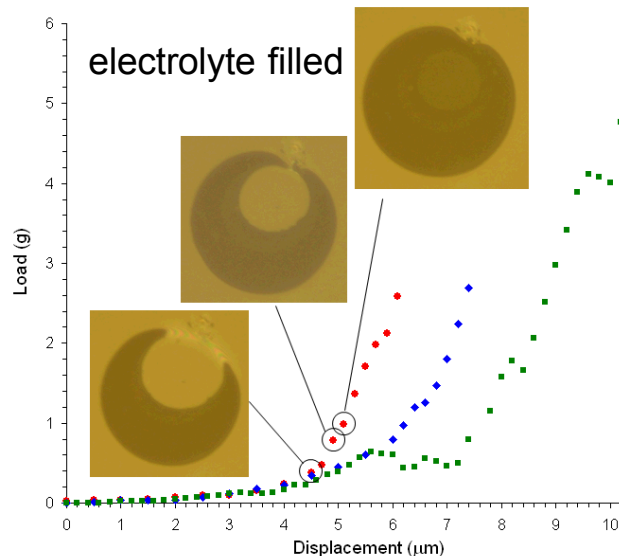
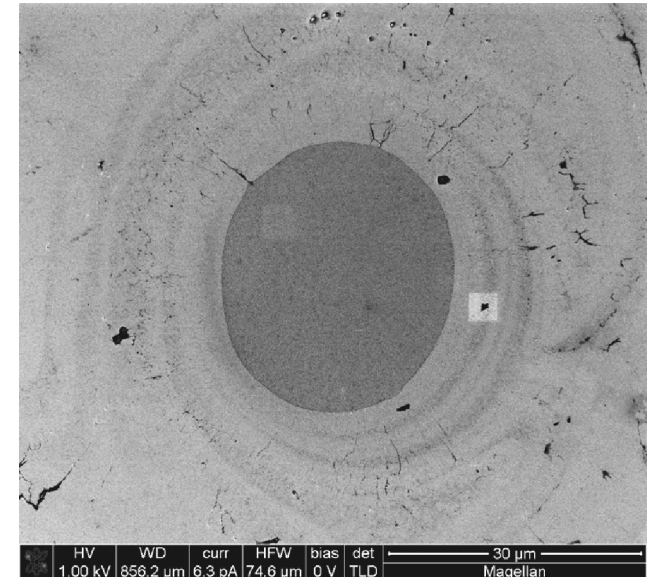


Model oxides may represent one way of probing the limiting cases of defect chemistry

Can more detail be learned by restricting area to enable imaging?



Snapshot approach

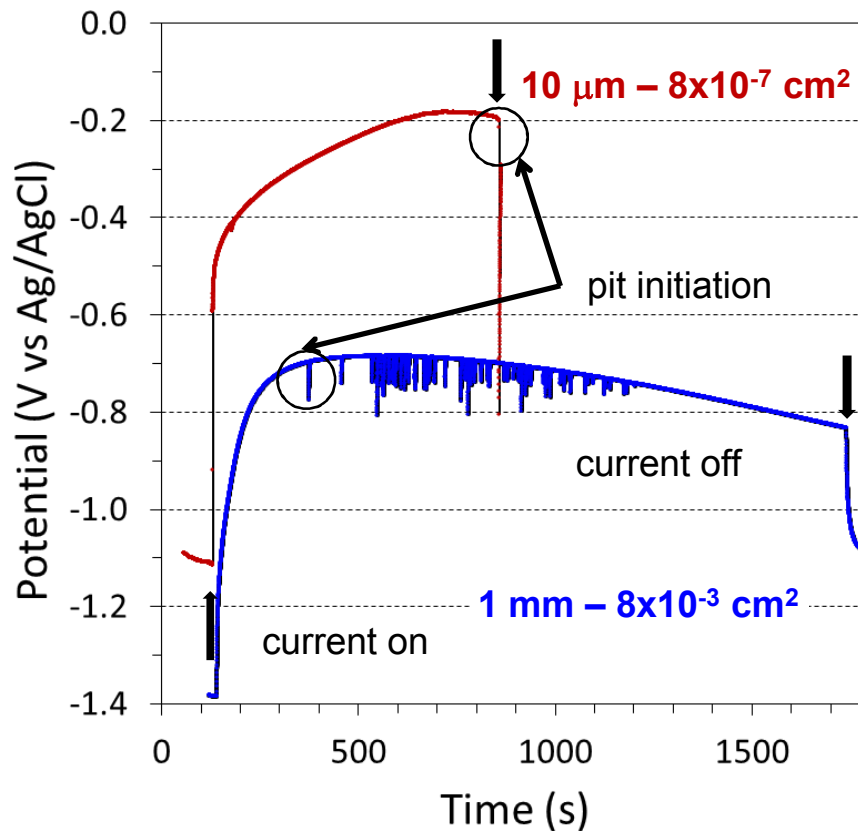


Size limits – leak free seals with minimal under seal activity at 5 - 20 μm diameter, $1 \times 10^{-7} - 1 \times 10^{-6} \text{ cm}^2$

Current limits – galvanostatic polarization at relevant current densities

Microcell Measurements Yield Meaningful Data

Potential response to a current stimulus is consistent across 1 cm^2 to $2 \times 10^{-7} \text{ cm}^2$



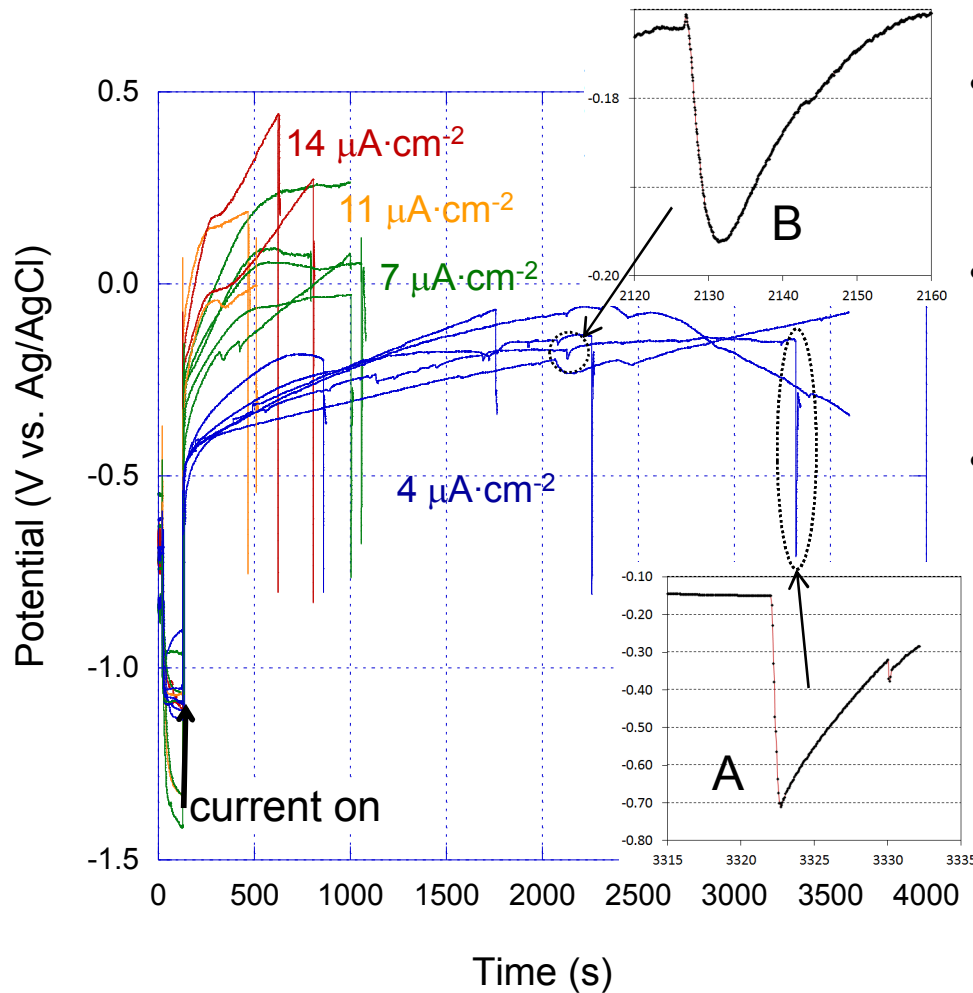
Single events are isolated with small areas

Reduced current – limited available to accelerate pit growth



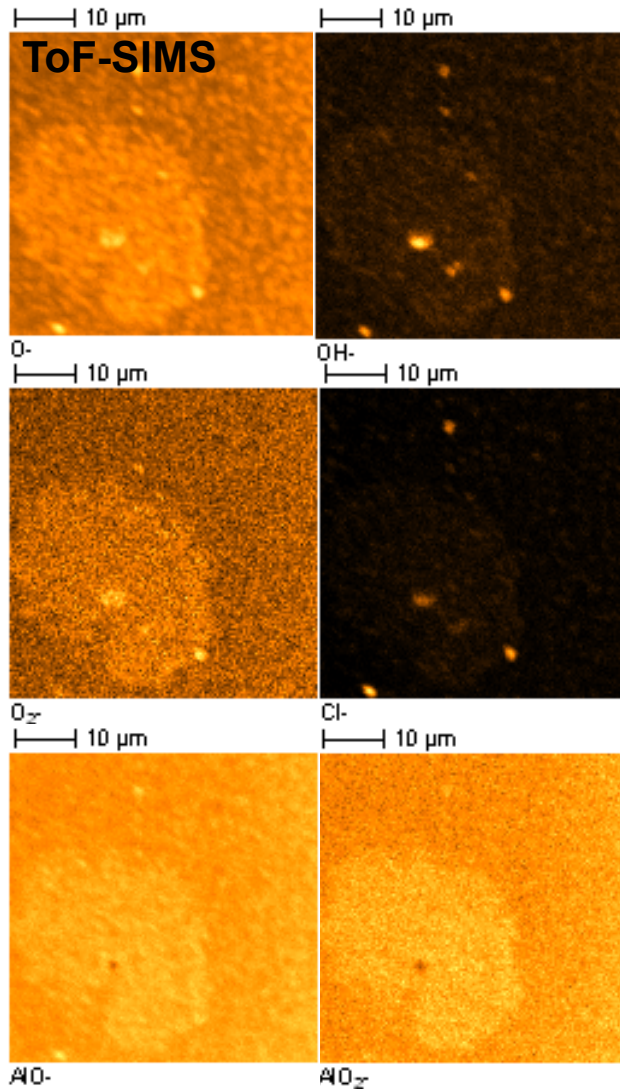
Possible opportunity to characterize initiation sites

Attributes of Single Discharge Event Experiments

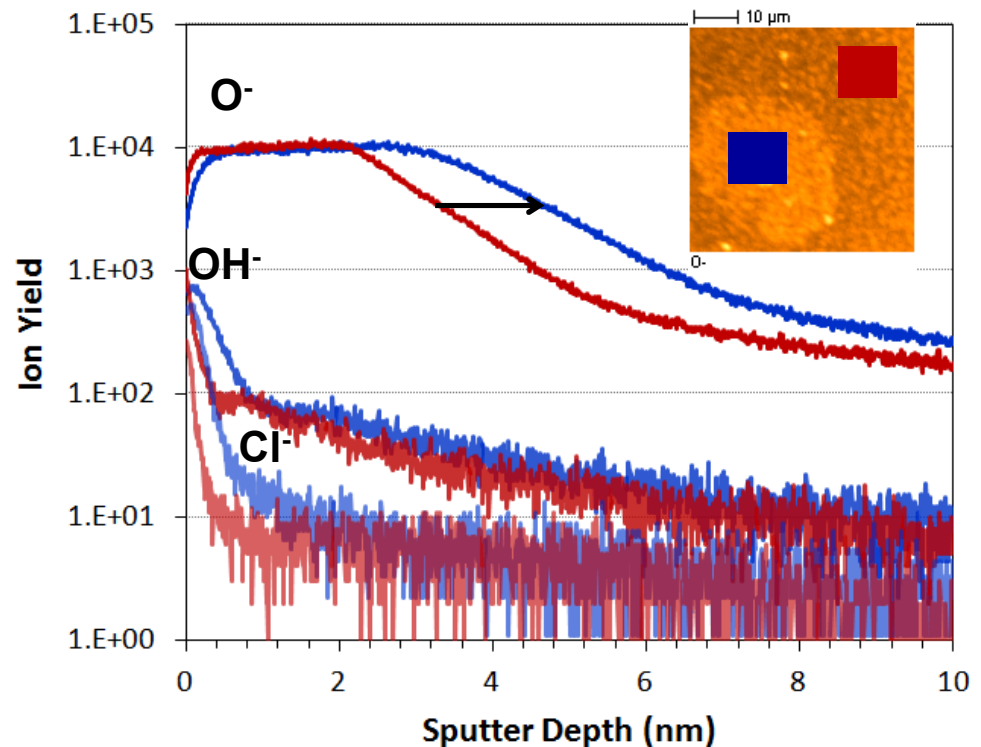


- Increased applied current density – higher probability of creating an event
- increased applied current density - shorter induction time for event occurrence
- Two types of depolarization signatures
 - large magnitude discharge events (A)
 - small magnitude or extended time perturbations (B)

Polarization drives oxide growth with minimal compositional change to the film



- Oxide growth: 10% from electrolyte immersion, 20 to 40% with polarization
- Cl^- primarily restricted to the hydrated outer layer

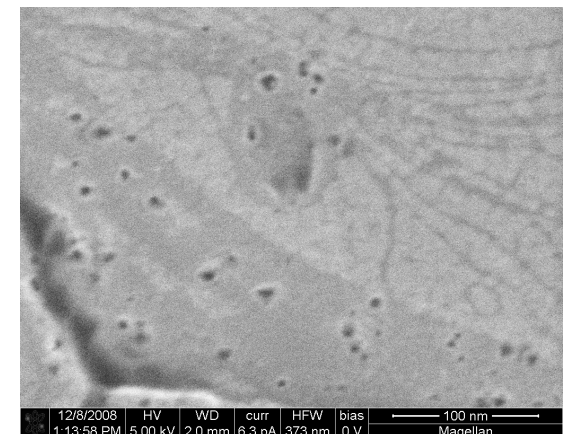
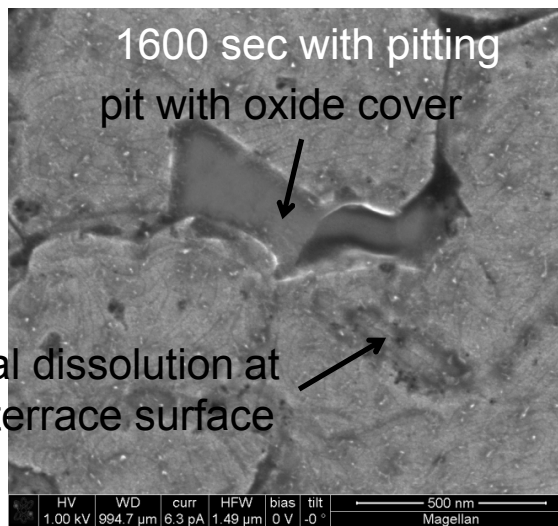
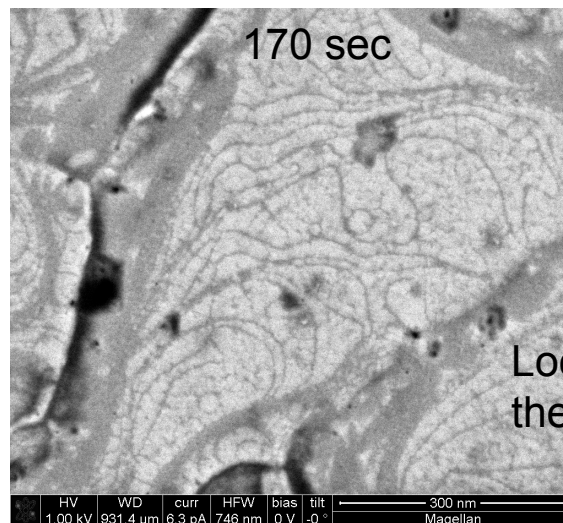
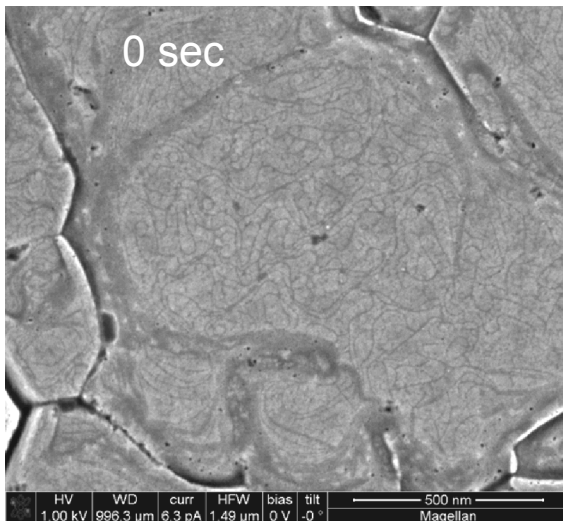
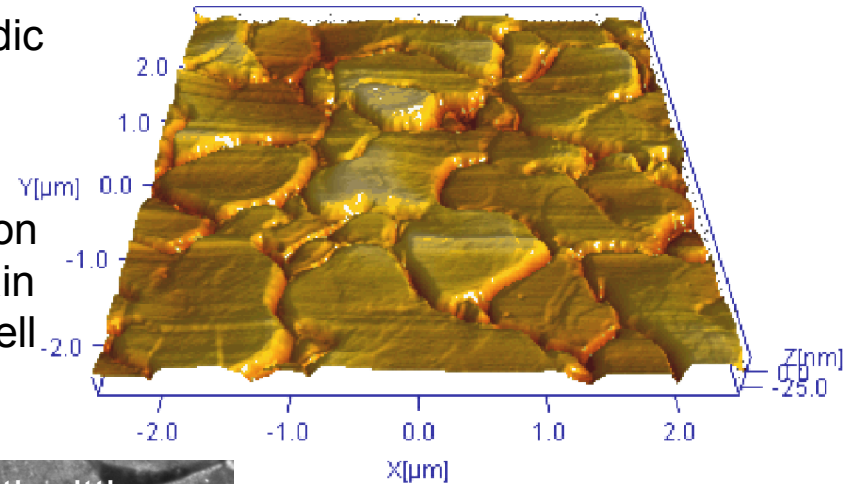


Structural impact of polarization is greatest at the high step density facets of the grains

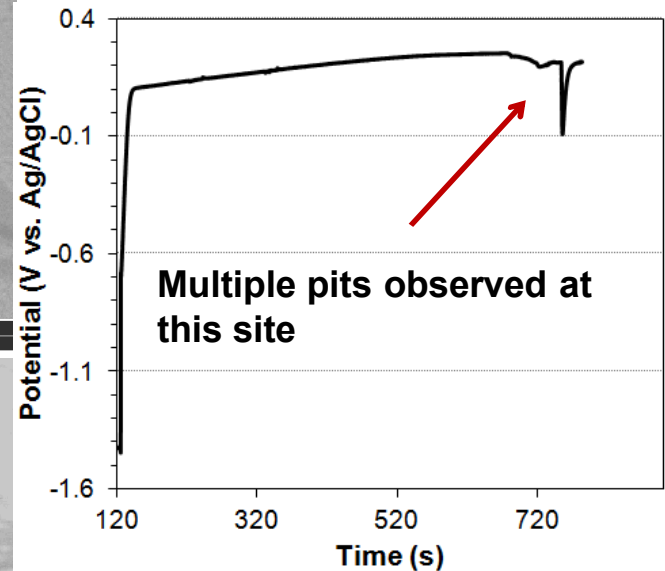
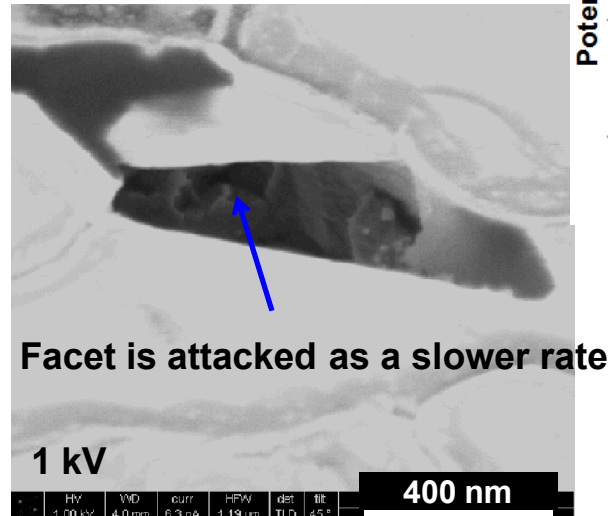
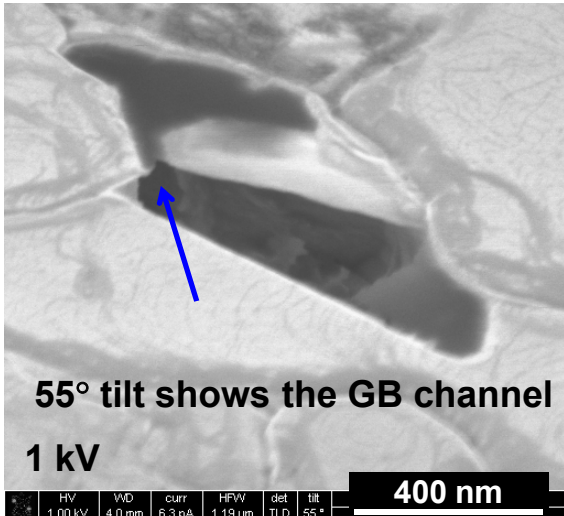
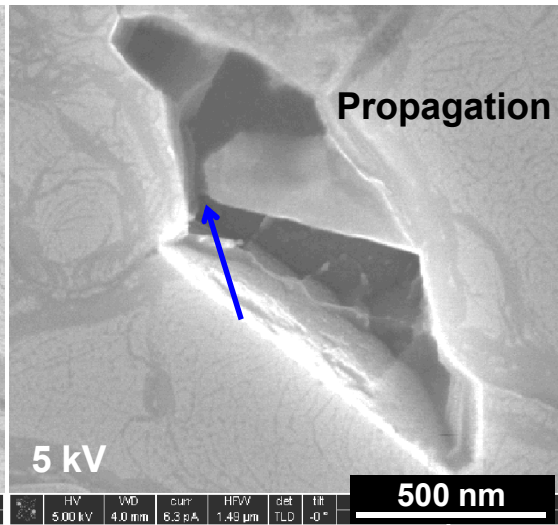
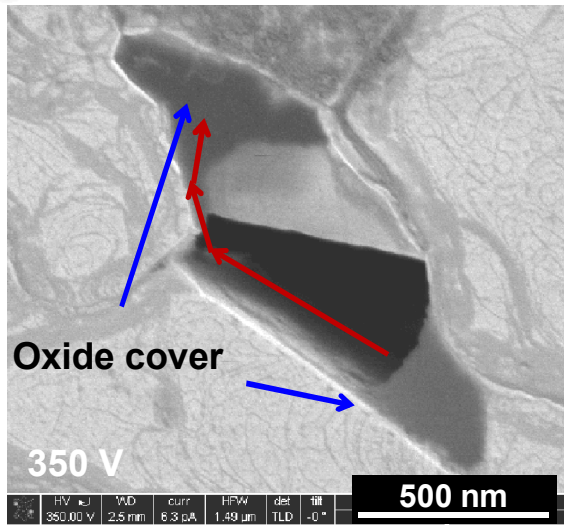
700 nm thick Al(111) film in de-aerated 50 mM NaCl pH 7
– larger grains for better spatial discrimination

$0.6 \mu\text{A}\cdot\text{cm}^{-2}$ anodic
polarization for
variable time

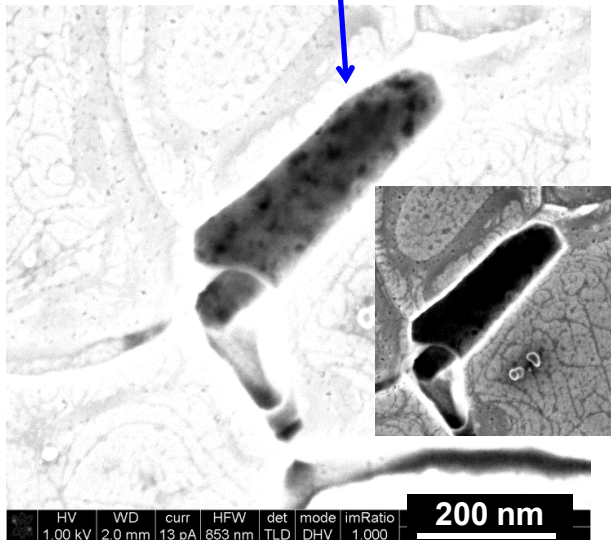
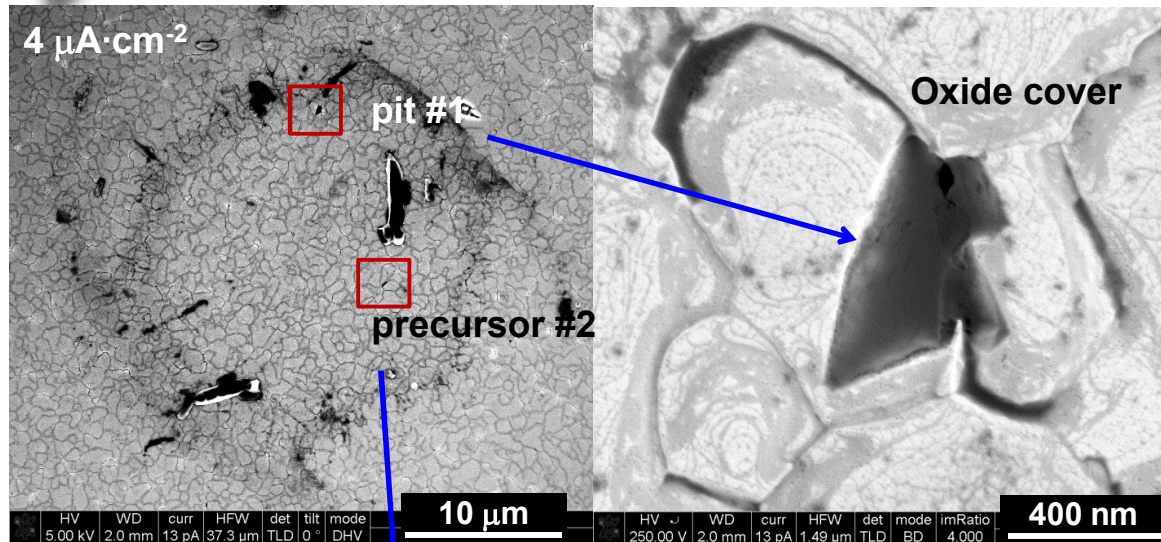
void/pores form on
contours into grain
boundaries as well
as terraces



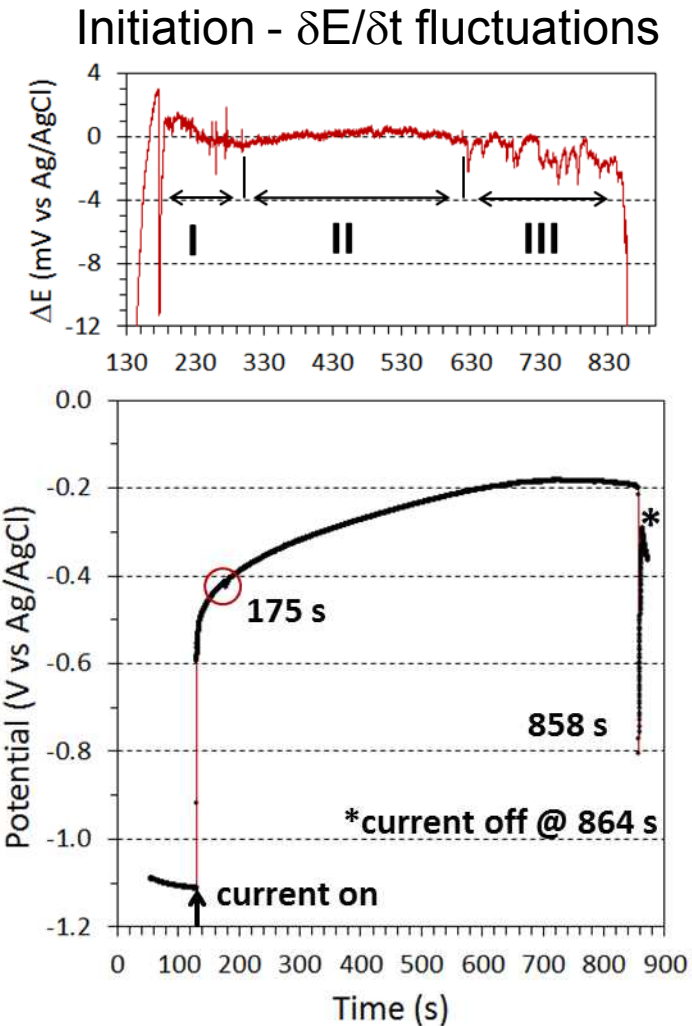
Evolved pits possess compliant oxide covers



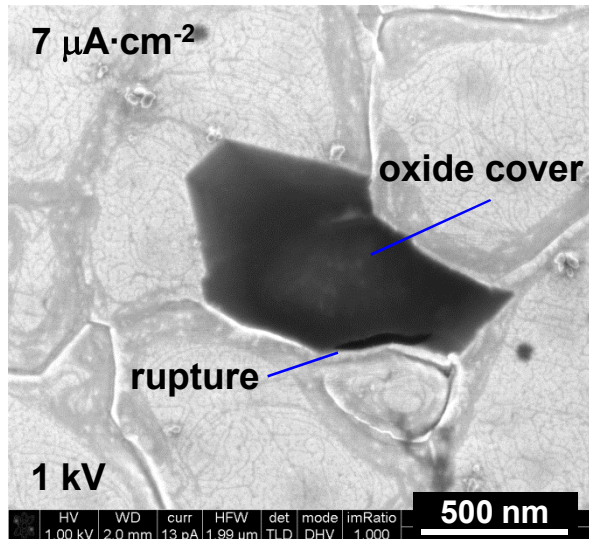
Sufficient current becomes localized to drive early stage pit formation



- Initiation sites – high topographic gradient (GBs)
- Void/pore formation is most prevalent in same regions
- Multiple initiation sites can be active concurrently

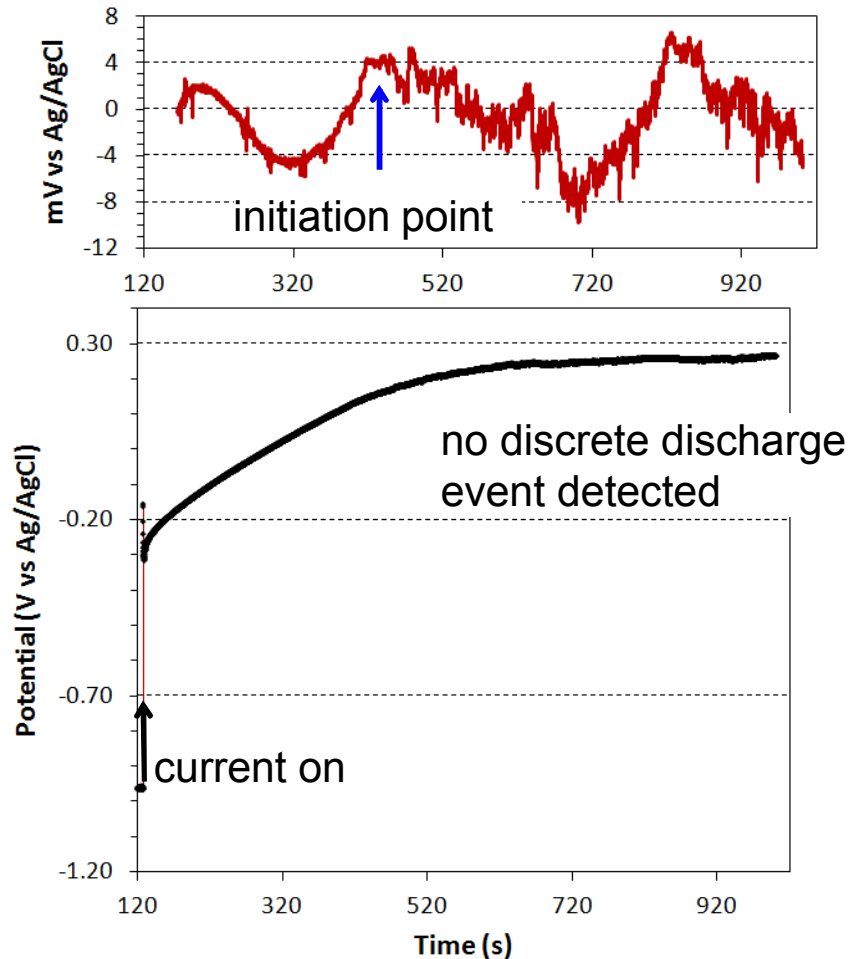


Electrochemical noise may also signal slow growth of an early stage pit

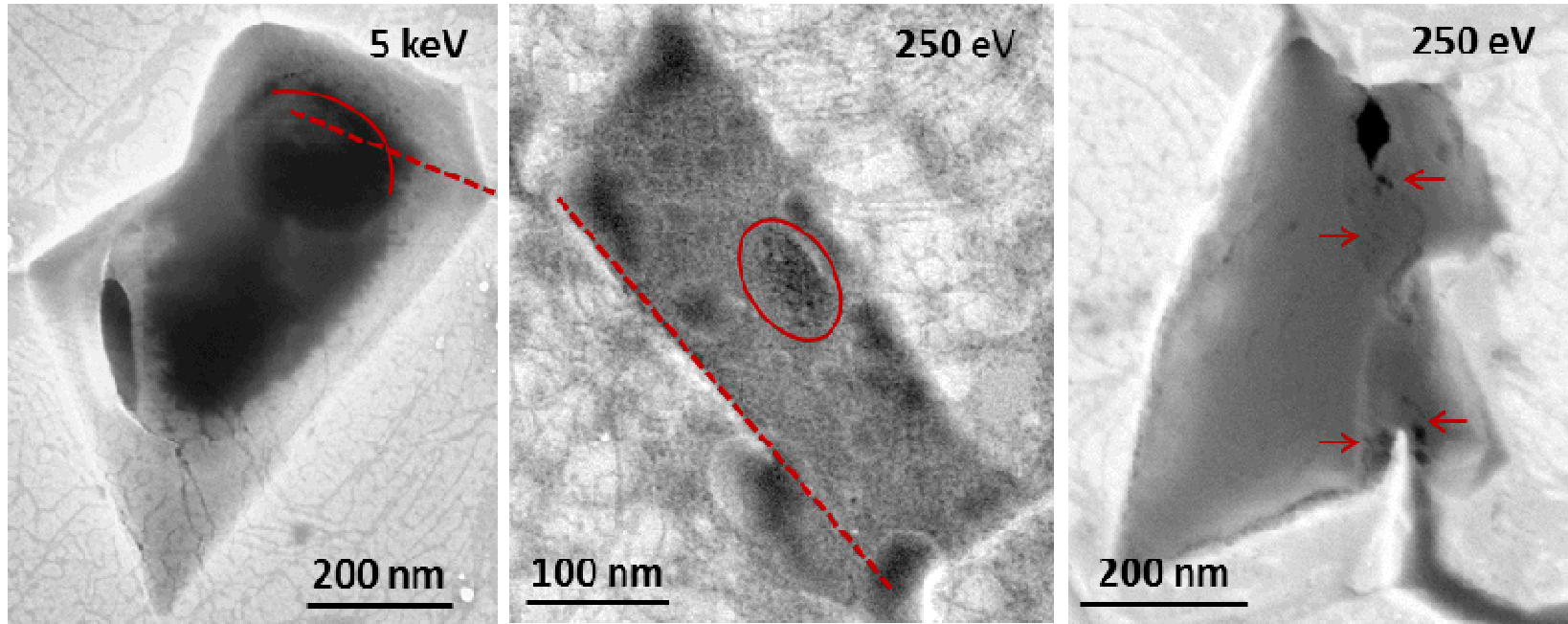


An occluded pit is observed despite the absence of a significant magnitude discharge event

- EC noise is a better indicator of micro-cell activity



Early stage pits: oxide membranes possess pore clusters

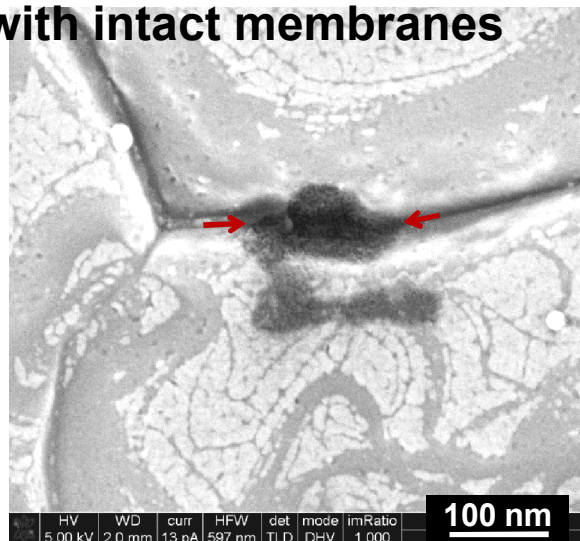
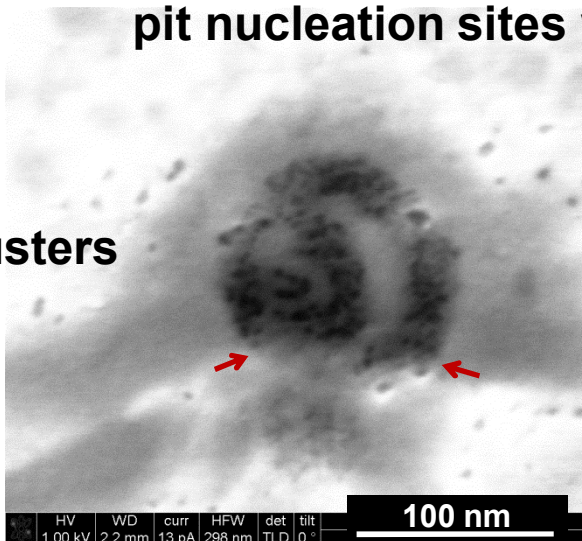


pore clusters appear near grain boundaries

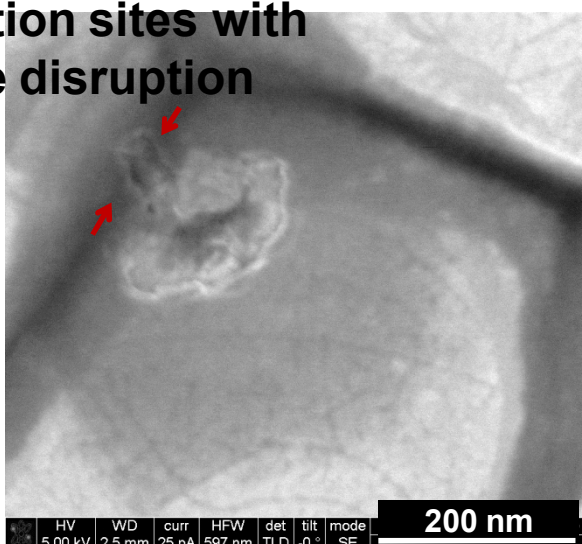
Pit precursors: concentrated pore clusters are common for high gradient regions

pit nucleation sites with intact membranes

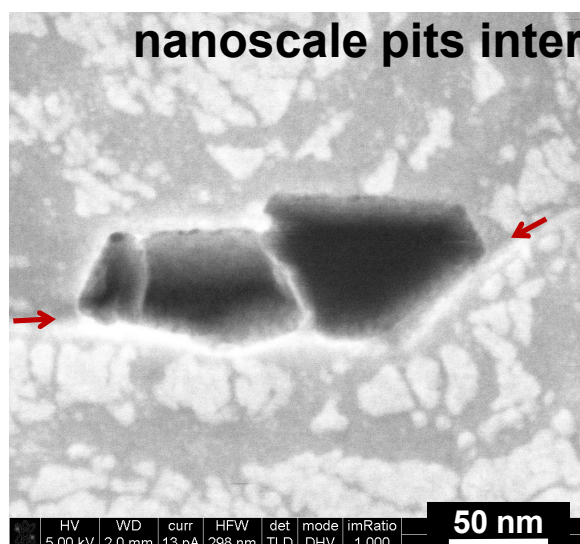
pore clusters



pit nucleation sites with membrane disruption

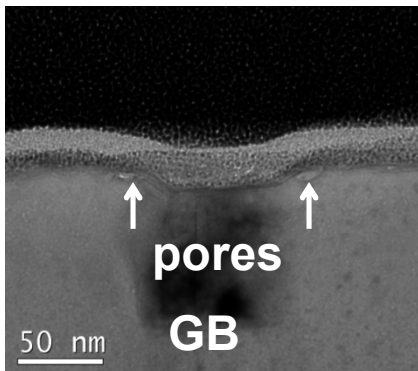
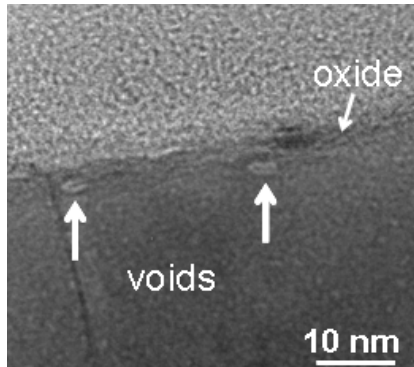


nanoscale pits internal to a grain



Interfacial Voids as Pit Precursors

Precursor sites
preferentially at emergent
facets



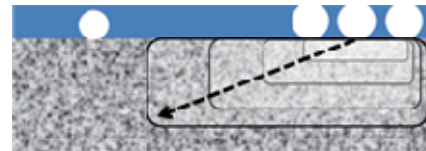
Void nucleation



Void growth and pore formation



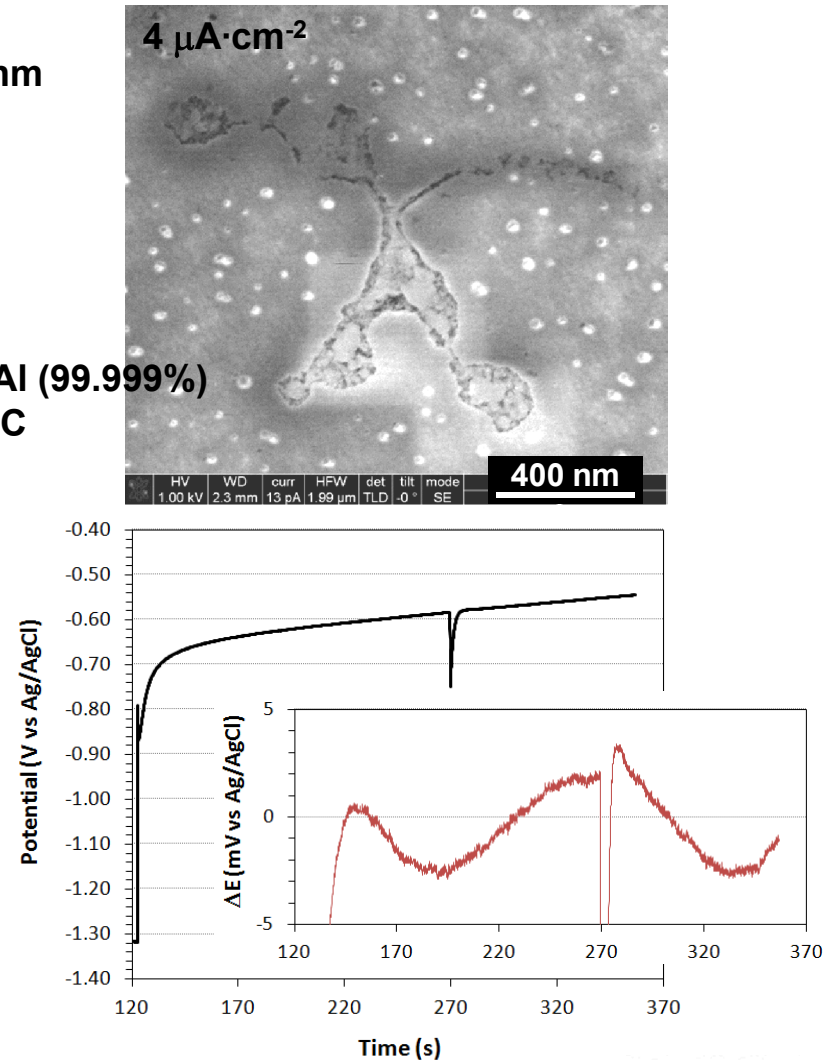
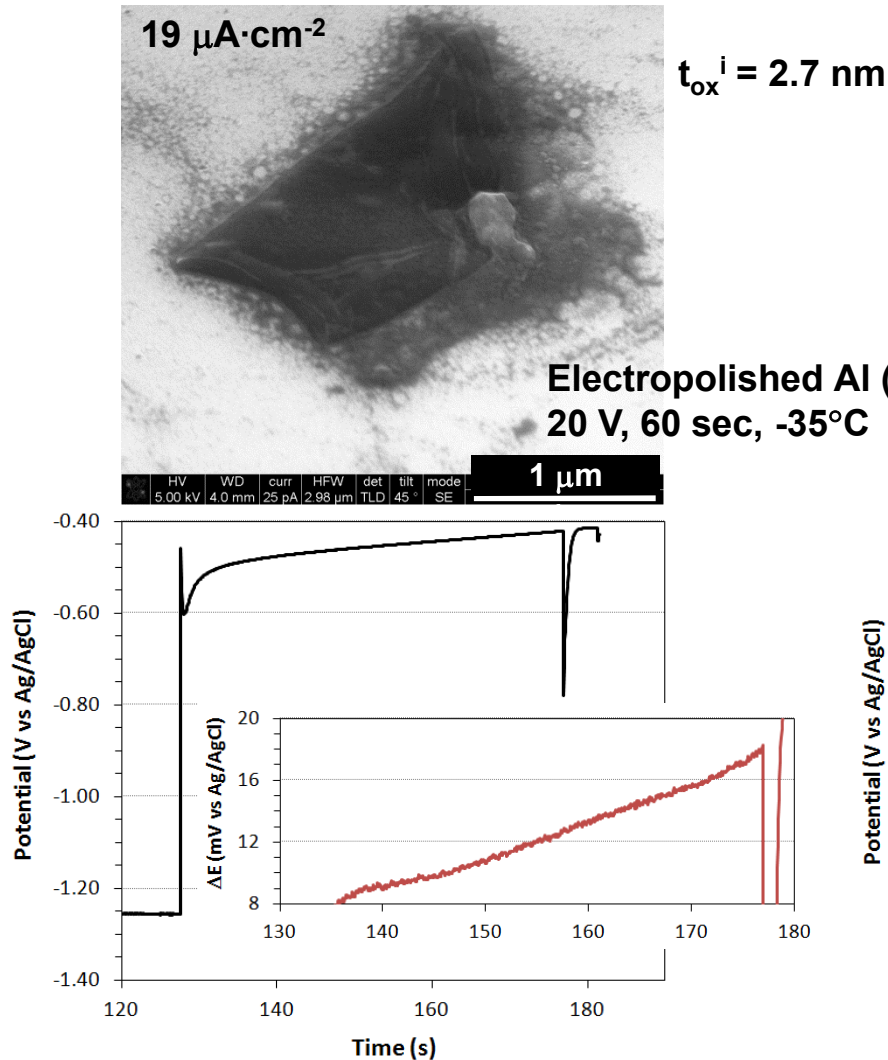
Stable cluster formation – oxide perforation



Pit nucleation under oxide membrane

- O vacancy saturation and interfacial stress produces voids
- higher step densities – lower ionization barrier for Al \Rightarrow emergent facets more active
- steps serve to lower void nucleation barrier
- voids grow into pores
- initiation occurs – stress due to local topology – destabilizes the pore cluster toward passivation

Hydrous oxides yield similar responses

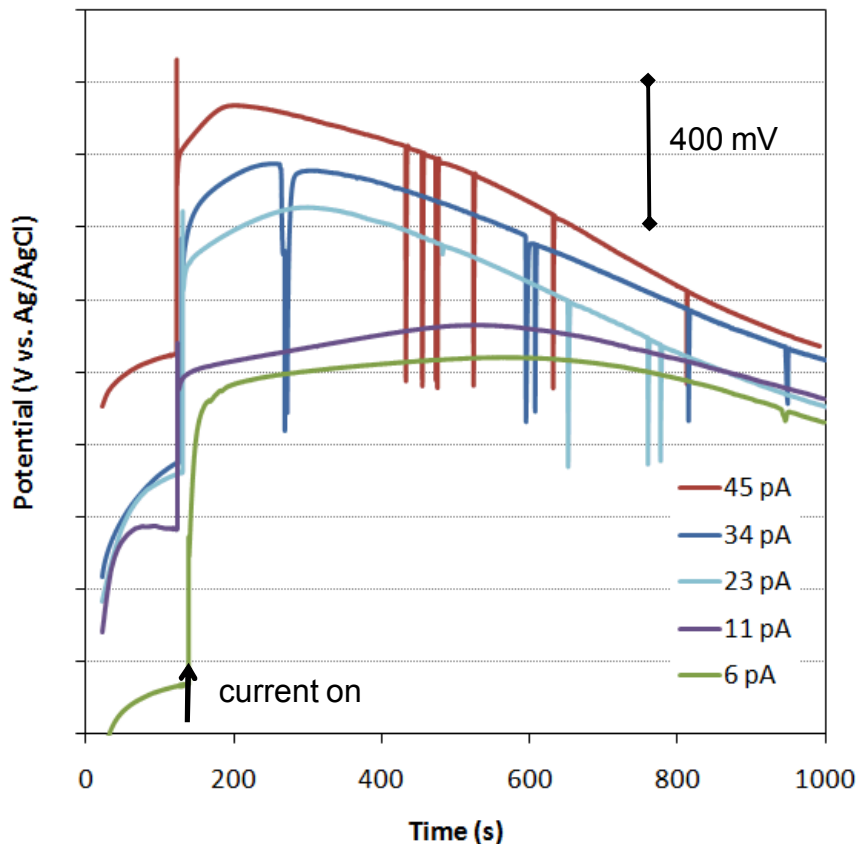




Back-up Slides

Defect and breakdown signatures are measureable in the micro-cell

Anodic polarization using a 20 μm diameter capillary



i (pA)	j ($\mu\text{A}\cdot\text{cm}^{-2}$)	t_{max} (s)	E_{max}^* (mV)	events
45	15	73	45	multiple, frequent
34	11	125	-38	multiple, frequent
23	7	320	-82	multiple, infrequent
11	4	480	-172	multiple, infrequent
6	2	450	-159	single, rarely
3	1	1930	-252	none detected

*vs. Ag/AgCl

Defect response is observed with anodic polarization

Breakdown events are observed at potentials > -550 mV vs. Ag/AgCl

Likelihood of a breakdown event scales with current magnitude

Drive single breakdown events – characterize the event signature – correlate events with evolved surface structure